

## **BC847BS**

#### **Dual NPN Small Signal Transistor**

#### **Features**

• Epoxy meets UL-94 V-0 flammability rating

• Surface mount package ideally Suited for Automatic Insertion

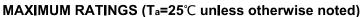
#### **Mechanical Data**

• Package: SOT-363

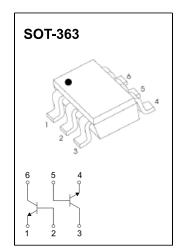
• Terminals: Tin plated leads, solderable per

J-STD-002 and JESD22-B102

• Marking:1F



Symbol	Parameter	Value	Unit	
Vсво	Collector-Base Voltage	50		
VCEO	Collector-Emitter Voltage	45	V	
VEBO	Emitter-Base Voltage	6		
<b>I</b> c	Collector Current-Continuous	100	mA	
Po	Power Dissipation	200	mW	
RөJA	Thermal Resistance. Junction to Ambient	625	°C/W	
$T_J, T_stg$	Operation Junction and Storage Temperature Range	-55~+150	°C	



**ELECTRICAL CHARACTERISTICS (T<sub>a</sub>=25°C unless otherwise specified)** 

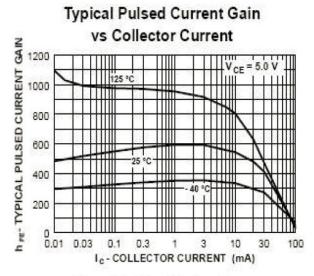
Parameter	Symbol	Test conditions	Min	Тур	Max	Unit	
Collector-base breakdown voltage	V(BR)CBO	I <sub>C</sub> =10μA,I <sub>E</sub> =0	50			V	
Collector-emitter breakdown voltage	V(BR)CEO	I <sub>C</sub> =1mA,I <sub>B</sub> =0	45			<b>V</b>	
Emitter-base breakdown voltage	V(BR)EBO	I <sub>E</sub> =10μA,I <sub>C</sub> =0	6			٧	
Collector cut-off current	Ісво	V <sub>CB</sub> =30V,I <sub>E</sub> =0			15		
Emitter cut-off current	I <sub>EBO</sub>	V <sub>EB</sub> =4V, I <sub>C</sub> =0			15	nA	
DC current gain*	h <sub>FE</sub>	V <sub>CE</sub> =5V,I <sub>C</sub> =2mA	200		450		
Calleston and then actuation values	VCE(sat)(1)	I <sub>C</sub> =10mA,I <sub>B</sub> =0.5mA			0.25	V	
Collector-emitter saturation voltage	VCE(sat)(2)	I <sub>C</sub> =100mA,I <sub>B</sub> =5mA			0.65	٧	
Dana and the same	VBE(1)	V <sub>CE</sub> =5V,I <sub>C</sub> =2mA	0.58		0.7	٧	
Base-emitter voltage	V <sub>BE(2)</sub>	V <sub>CE</sub> =5V,I <sub>C</sub> =10mA			0.77	٧	
Transition frequency	f <sub>T</sub>	V <sub>CE</sub> =5V,I <sub>C</sub> =20mA ,f=100MHz		200		MHz	
Collector output capacitance	Соь	V <sub>CB</sub> =10V,I <sub>E</sub> =0,f=1MHz		2		pF	

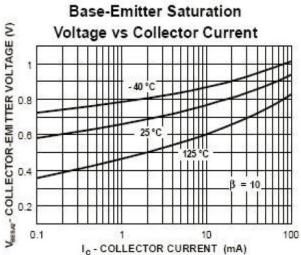
<sup>\*</sup>pulse test: Pulse Width ≤300µs, Duty Cycle≤ 2.0%.

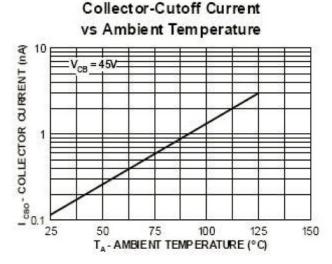
## **BC847BS**

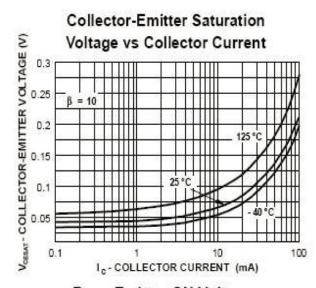
#### **Dual NPN Small Signal Transistor**

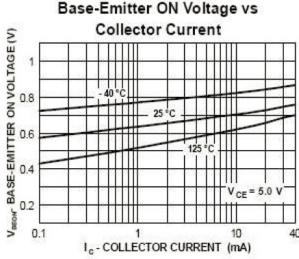
#### **Typical Characteristics**

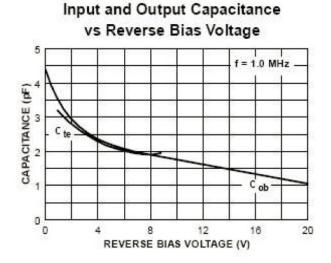








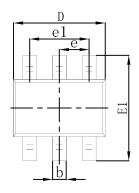


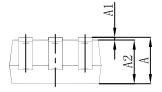


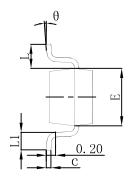
# **BC847BS**

#### **Dual NPN Small Signal Transistor**

### **SOT-363 Package Outline Dimensions**

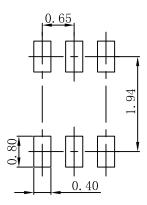






Symbol	Dimensions In Millimeters		Dimensions In Inches		
	Min	Max	Min	Max	
Α	0.900	1.100	0.035	0.043	
A1	0.000	0.100	0.000	0.004	
A2	0.900	1.000	0.035	0.039	
b	0.150	0.350	0.006	0.014	
С	0.100	0.150	0.004	0.006	
D	2.000	2.200	0.079	0.087	
E	1.150	1.350	0.045	0.053	
E1	2.150	2.400	0.085	0.094	
е	0.650 TYP		0.026 TYP		
e1	1.200	1.400	0.047	0.055	
L	0.525 REF		0.021 REF		
L1	0.260	0.460	0.010	0.018	
θ	0°	8°	0°	8°	

### **SOT-363 Suggested Pad Layout**



#### Note:

- 1.Controlling dimension:in millimeters.
- 2.General tolerance:±0.05mm.
- 3. The pad layout is for reference purposes only.